

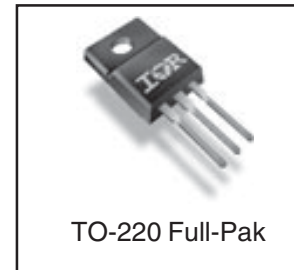
Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Motor Drive

V_{DSS}	$R_{DS(on)}$ typ.	T_{rr} typ.	I_D
500V	0.67 Ω	73ns	4.7A

Benefits

- Low Gate Charge Q_g results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	4.7	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	3.0	
I_{DM}	Pulsed Drain Current ①	16	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	42	W
	Linear Derating Factor	0.33	W/ $^\circ\text{C}$
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	13	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	$^\circ\text{C}$
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	4.7	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	16		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}$, $I_S = 4.0\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	73	110	ns	$T_J = 25^\circ\text{C}$ $I_F = 4.0\text{A}$
		—	99	150		$T_J = 125^\circ\text{C}$ $di/dt = 100\text{A}/\mu\text{s}$ ④
Q_{rr}	Reverse Recovery Charge	—	200	310	nC	$T_J = 25^\circ\text{C}$
		—	360	540		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	6.7	10	A	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

IRFIB5N50L

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$BV_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.43	—	V/°C	Reference to 25°C , $I_D = 1mA$ ⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.67	0.80	Ω	$V_{GS} = 10V, I_D = 2.4A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	50	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	2.0	mA	$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	2.8	—	—	S	$V_{DS} = 50V, I_D = 2.4A$
Q_g	Total Gate Charge	—	—	45	nC	$I_D = 4.0A$
Q_{gs}	Gate-to-Source Charge	—	—	13		$V_{DS} = 400V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	23		$V_{GS} = 10V$, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	13	—	ns	$V_{DD} = 250V$
t_r	Rise Time	—	17	—		$I_D = 4.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	26	—		$R_G = 9.0\Omega$
t_f	Fall Time	—	10	—		$V_{GS} = 10V$, See Fig. 10 ④
C_{iss}	Input Capacitance	—	1000	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	110	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	12	—		$f = 1.0MHz$, See Fig. 5
C_{oss}	Output Capacitance	—	1360	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	31	—		$V_{GS} = 0V, V_{DS} = 400V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	75	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$ ⑤

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	140	mJ
I_{AR}	Avalanche Current①	—	4.0	A
E_{AR}	Repetitive Avalanche Energy①	—	3.0	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	3.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	65	

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11).
- ② Starting $T_J = 25^\circ\text{C}$, $L = 18mH$, $R_G = 25\Omega$, $I_{AS} = 4.0A$, $dv/dt = 13V/ns$ (See Figure 12a).
- ③ $I_{SD} \leq 4.0$, $di/dt \leq 280A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

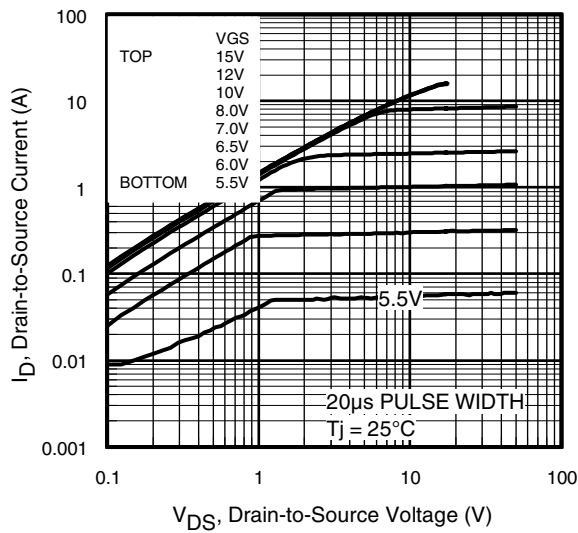


Fig 1. Typical Output Characteristics

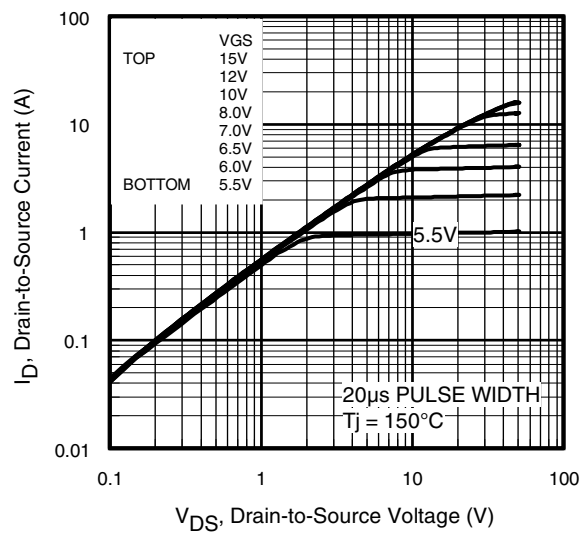


Fig 2. Typical Output Characteristics

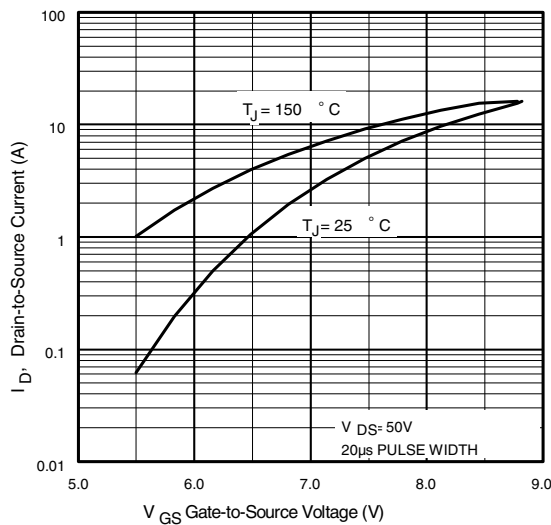


Fig 3. Typical Transfer Characteristics

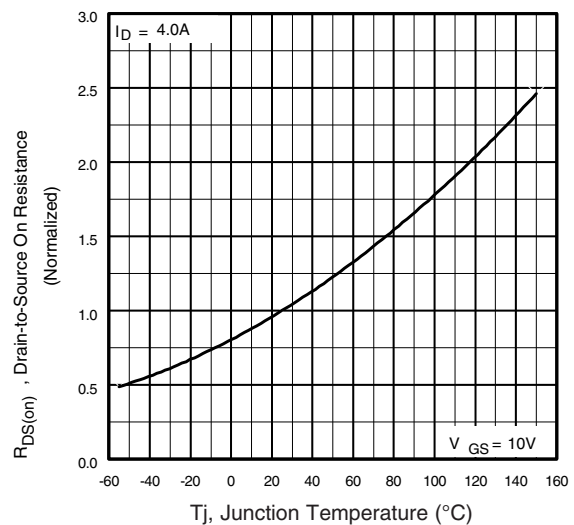


Fig 4. Normalized On-Resistance vs. Temperature

IRFIB5N50L

International
IR Rectifier

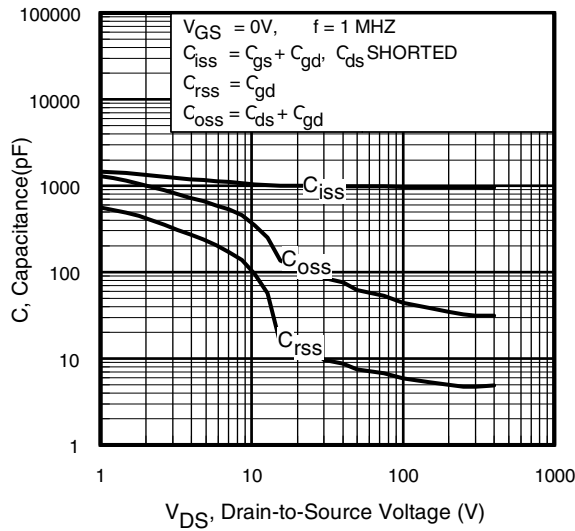


Fig 5. Typical Capacitance vs.
Drain-to-Source Voltage

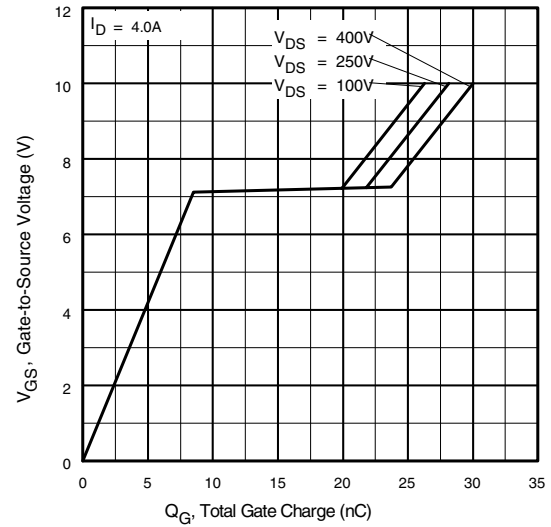


Fig 6. Typical Gate Charge vs.
Gate-to-Source Voltage

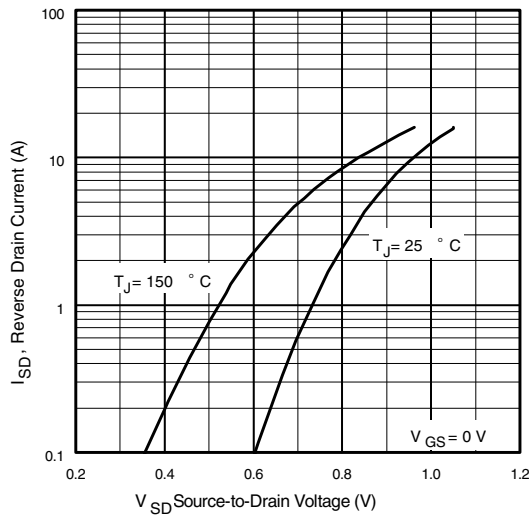


Fig 7. Typical Source-Drain Diode
Forward Voltage

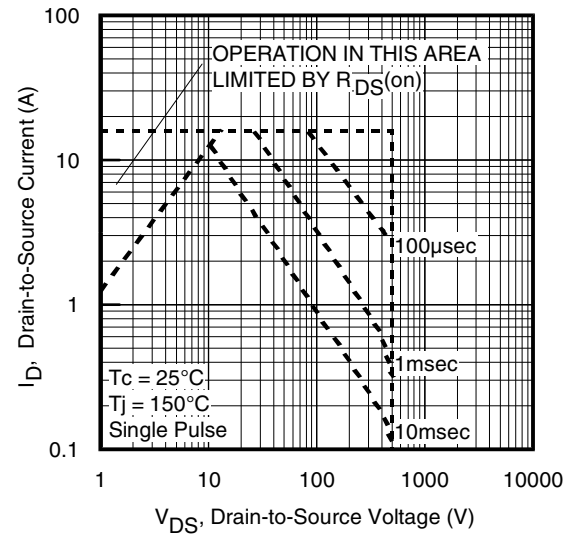


Fig 8. Maximum Safe Operating Area

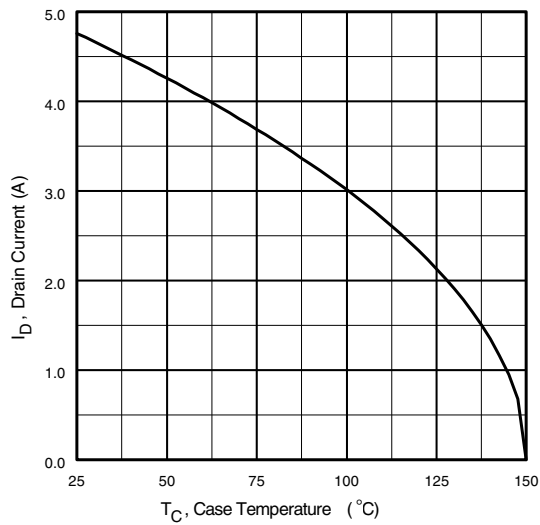


Fig 9. Maximum Drain Current vs. Case Temperature

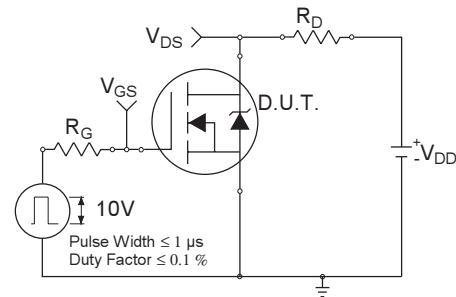


Fig 10a. Switching Time Test Circuit

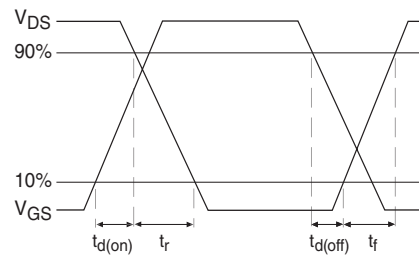


Fig 10b. Switching Time Waveforms

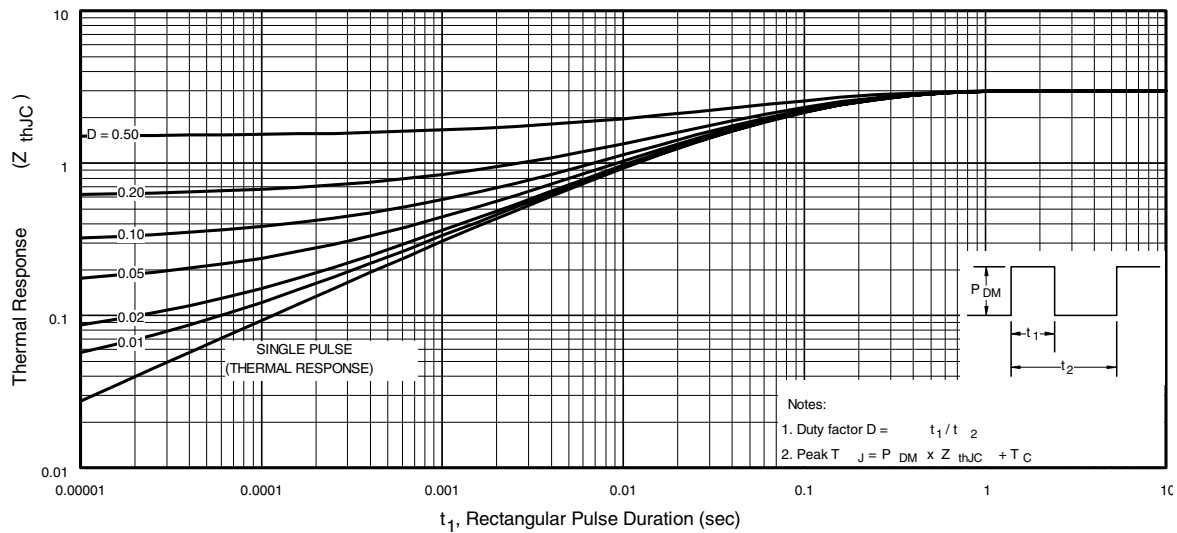


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRFIB5N50L

International
IR Rectifier

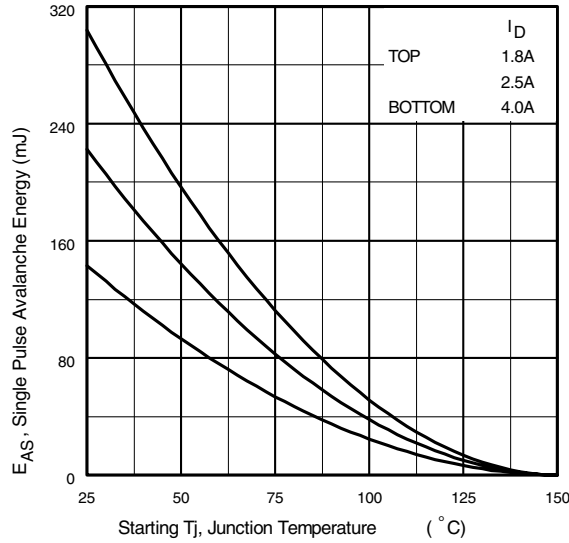


Fig 12a. Maximum Avalanche Energy vs. Drain Current

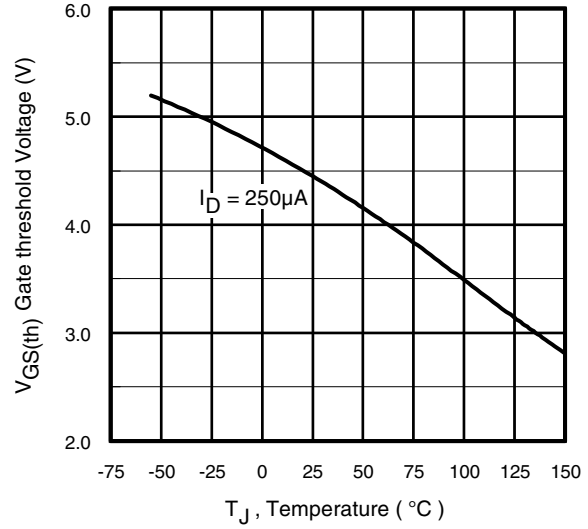


Fig 14. Threshold Voltage vs. Temperature

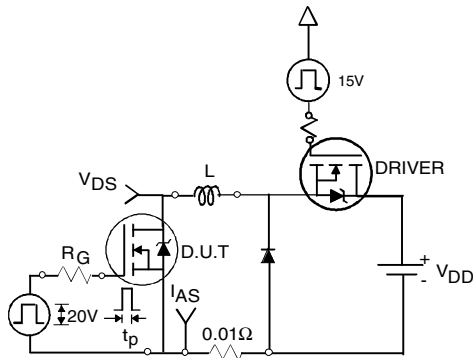


Fig 12c. Unclamped Inductive Test Circuit

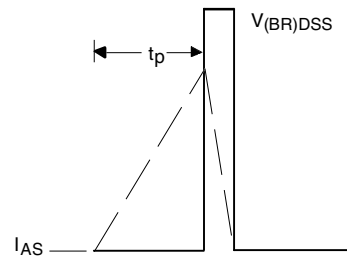


Fig 12d. Unclamped Inductive Waveforms

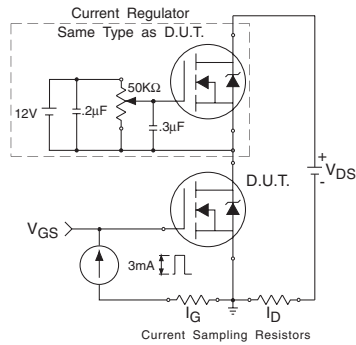


Fig 13a. Gate Charge Test Circuit

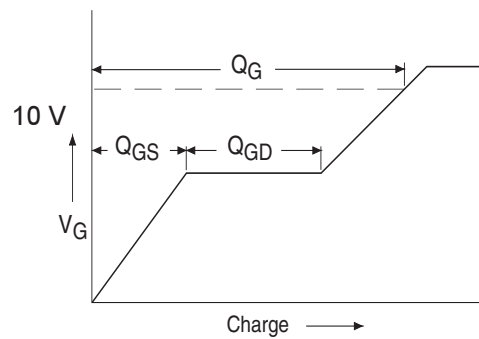
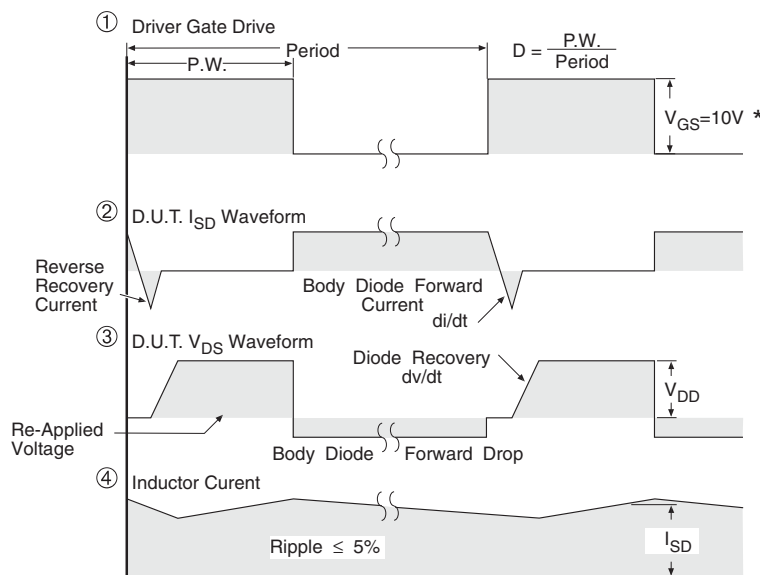
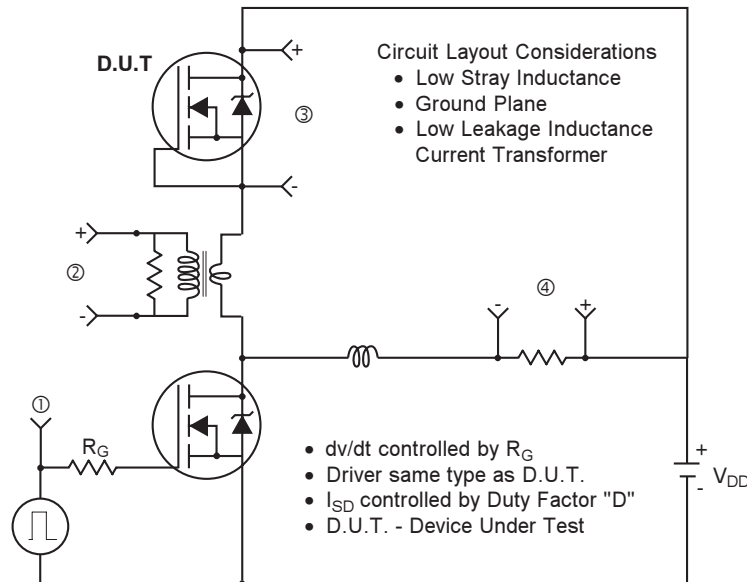


Fig 13b. Basic Gate Charge Waveform
www.irf.com

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

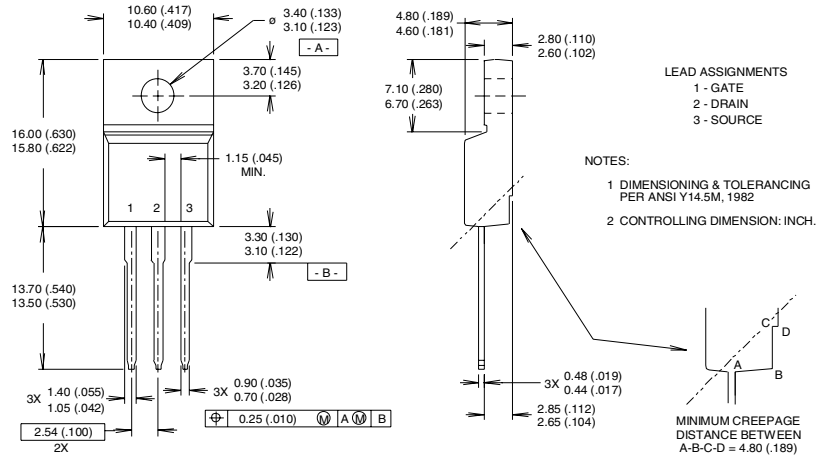
Fig 14. For N-Channel HEXFET® Power MOSFETs

IRFIB5N50L

International
IR Rectifier

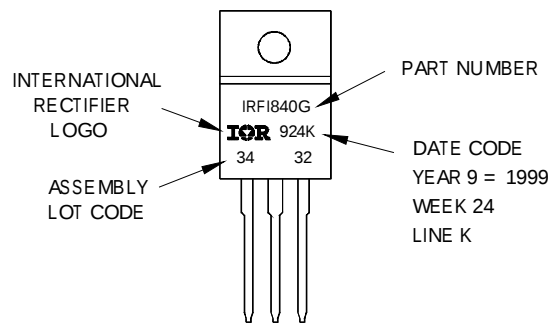
TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI840G
WITH ASSEMBLY
LOT CODE 3432
ASSEMBLED ON WW 24 1999
IN THE ASSEMBLY LINE "K"



Super TO-220 Full-Pak package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Automotive [Q101] market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.09/02

www.irf.com